

## N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STY30NA50	500 V	< 0.175 Ω	30 A

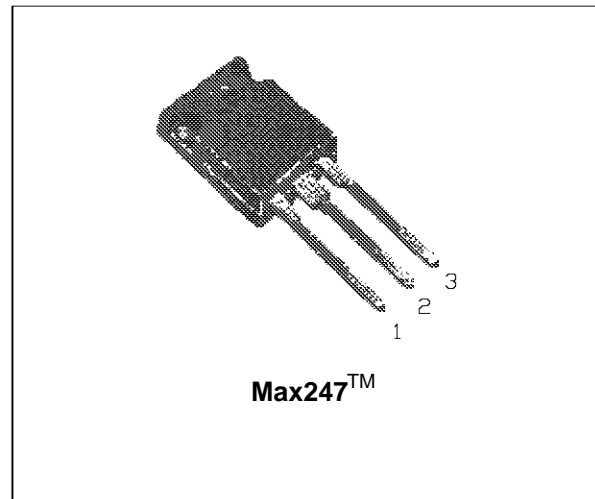
- TYPICAL R<sub>DS(on)</sub> = 0.15 Ω
- EFFICIENT AND RELIABLE MOUNTING THROUGH CLIP
- ± 30V GATE TO SOURCE VOLTAGE RATING
- REPETITIVE AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

### DESCRIPTION

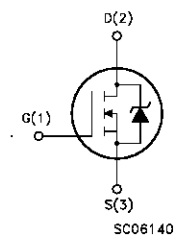
The Max247™ package is a new high volume power package exhibiting the same footprint as the industry standard TO-247, but designed to accommodate much larger silicon chips, normally supplied in bigger packages such as TO-264. The increased die capacity makes the device ideal to reduce component count in multiple paralleled designs and save board space with respect to larger packages.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES (UPS)



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	500	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	500	V
V <sub>GS</sub>	Gate-source Voltage	± 30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	30	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	19	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	120	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	300	W
	Derating Factor	2.4	W/°C
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

**THERMAL DATA**

$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.42	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	40	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-Heatsink with Conductive Grease	Typ	0.05	

**AVALANCHE CHARACTERISTICS**

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max, $\delta < 1\%$ )	30	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$ , $I_D = I_{AR}$ , $V_{DD} = 50 V$ )	3000	mJ
$E_{AR}$	Repetitive Avalanche Energy (pulse width limited by $T_j$ max, $\delta < 1\%$ )	180	mJ
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive ( $T_c = 100^{\circ}C$ , pulse width limited by $T_j$ max, $\delta < 1\%$ )	19	A

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise specified)

**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	500			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125^{\circ}C$			200 1000	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 30 V$			$\pm 100$	nA

**ON (\*)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10 V$ $I_D = 15 A$ $V_{GS} = 10 V$ $I_D = 15 A$ $T_c = 100^{\circ}C$		0.15	0.175 0.35	$\Omega$ $\Omega$
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	30			A

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 15 A$	25			S
$C_{iss}$	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		6150	8000	pF
$C_{oss}$	Output Capacitance			780	1000	pF
$C_{rss}$	Reverse Transfer Capacitance			220	290	pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 250\text{ V}$		40	55	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$		70	90	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 400\text{ V}$ $I_D = 30\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		240		A/ $\mu$ s
$Q_g$	Total Gate Charge	$V_{DD} = 400\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$		245	320	nC
$Q_{gs}$	Gate-Source Charge			27		nC
$Q_{gd}$	Gate-Drain Charge			120		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400\text{ V}$ $I_D = 30\text{ A}$		75	100	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		30	40	ns
$t_c$	Cross-over Time			110	145	ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				30	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				120	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 30\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 30\text{ A}$ $V_{DD} = 100\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ $T_j = 150\text{ }^\circ\text{C}$		800		ns
$Q_{rr}$	Reverse Recovery Charge			17.6		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			44		A

(\*) Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

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